

ABSTRACT

Semiconductor devices according to some example embodiments include: a substrate; first channel patterns and second channel patterns that are spaced apart from each other on the substrate; an insulation structure between the first channel patterns and the second channel patterns; a gate structure that surrounds the first channel patterns, the second channel patterns, and at least a part of the insulation structure; and a source/drain pattern that is at both sides of each of the first channel patterns and the second channel patterns, wherein the insulation structure includes a first embedded insulation layer that is between the first channel patterns and the second channel patterns and extend in a first direction and a second embedded insulation layer between the first embedded insulation layer and the first channel patterns, and portions of the second embedded insulation layer are spaced apart from each other in the first direction.

FIG. 1